Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 30
$R_{DS(on)}$ (Ω) at V_{GS} = - 10 V	0.010
$R_{DS(on)}$ (Ω) at V_{GS} = - 4.5 V	0.024
I_D (A)	- 50
Configuration	Single

FEATURES

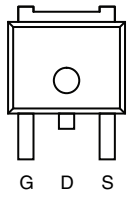
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified[d]
- 100 % R_g and UIS Tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

RoHS COMPLIANT

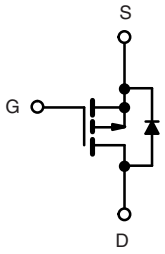
HALOGEN FREE

TO-252



Drain Connected to Tab

Top View



P-Channel MOSFET

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD45P03-12-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C[a]	I_D	- 50	A
	T_C = 125 °C		- 37	
Continuous Source Current (Diode Conduction)[a]		I_S	- 50	
Pulsed Drain Current[b]		I_{DM}	- 200	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 31	
Single Pulse Avalanche Energy		E_{AS}	48	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	71	W
	T_C = 125 °C		23	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	2.1	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).
d. Parametric verification ongoing.

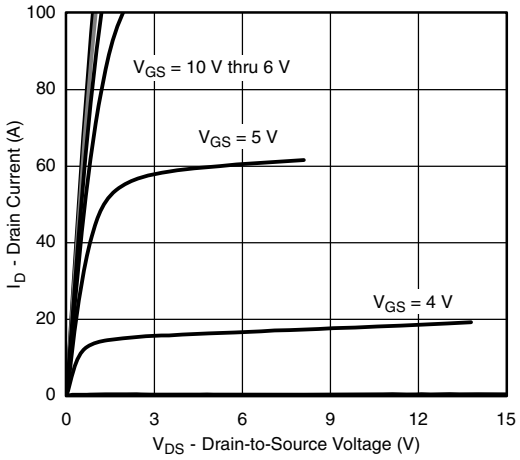
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0, I_D = - 250 µA		- 30	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA		- 1.5	- 2.0	- 2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = - 30 V	-	-	- 1	µA
		V_{GS} = 0 V	V_{DS} = - 30 V, T_J = 125 °C	-	-	- 50	
		V_{GS} = 0 V	V_{DS} = - 30 V, T_J = 175 °C	-	-	- 150	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = - 10 V	V_{DS} ≤ - 5 V	- 50	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V	I_D = - 15 A	-	0.008	0.010	Ω
		V_{GS} = - 10 V	I_D = - 15 A, T_J = 125 °C	-	-	0.015	
		V_{GS} = - 10 V	I_D = - 15 A, T_J = 175 °C	-	-	0.017	
		V_{GS} = - 4.5 V	I_D = - 12 A	-	0.019	0.024	
Forward Transconductance[b]	g_{fs}	V_{DS} = - 15 V, I_D = - 17 A		-	34	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = - 15 V, f = 1 MHz	-	2794	3495	pF
Output Capacitance	C_{oss}			-	616	770	
Reverse Transfer Capacitance	C_{rss}			-	470	590	
Total Gate Charge[c]	Q_g	V_{GS} = - 10 V	V_{DS} = - 15 V, I_D = - 45 A	-	55.3	83	nC
Gate-Source Charge[c]	Q_{gs}			-	7.3	-	
Gate-Drain Charge[c]	Q_{gd}			-	14	-	
Gate Resistance	R_g	f = 1 MHz		1.40	2.86	4.50	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 15 V, R_L = 0.33 Ω I_D ≅ - 45 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	11	16.5	ns
Rise Time[c]	t_r			-	11	16.5	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	29	43.5	
Fall Time[c]	t_f			-	19	28.5	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}			-	-	- 200	A
Forward Voltage	V_{SD}	I_F = - 40 A, V_{GS} = 0		-	- 0.9	- 1.5	V

Notes

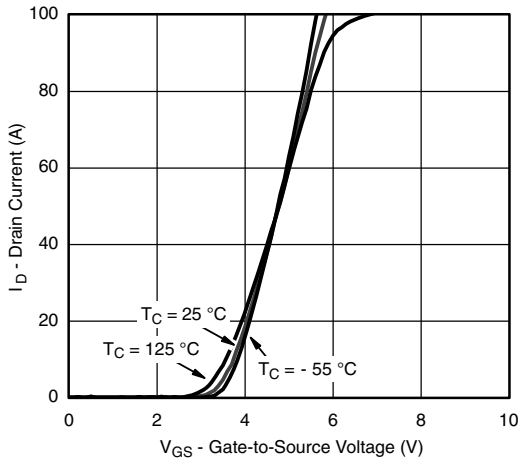
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

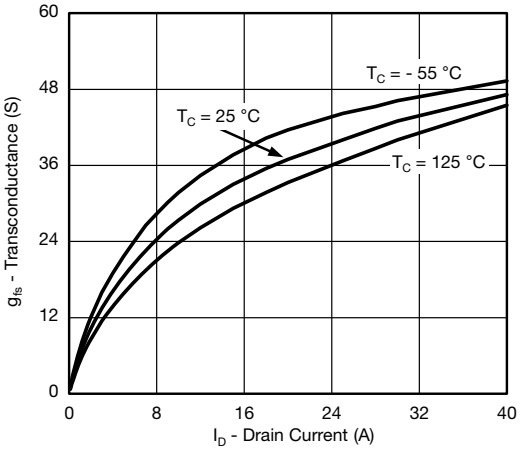
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



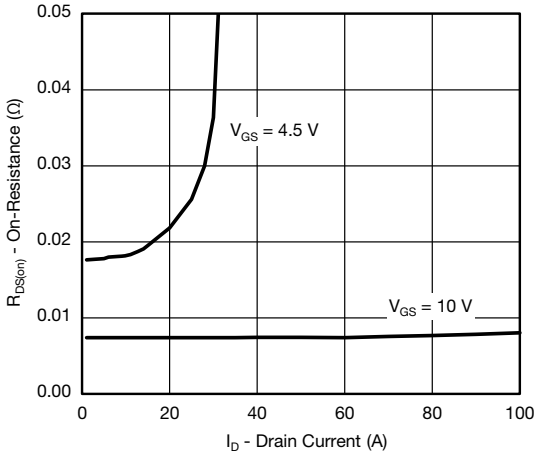
Output Characteristics



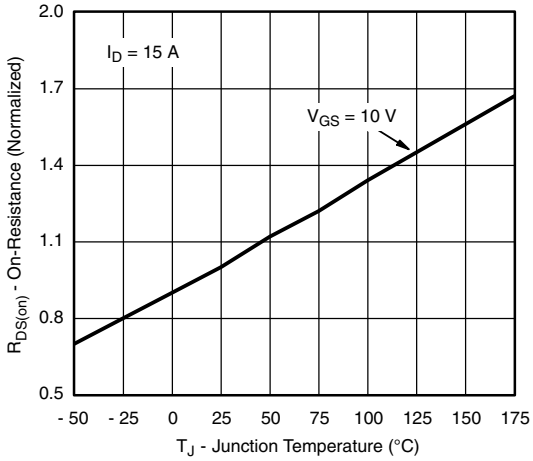
Transfer Characteristics



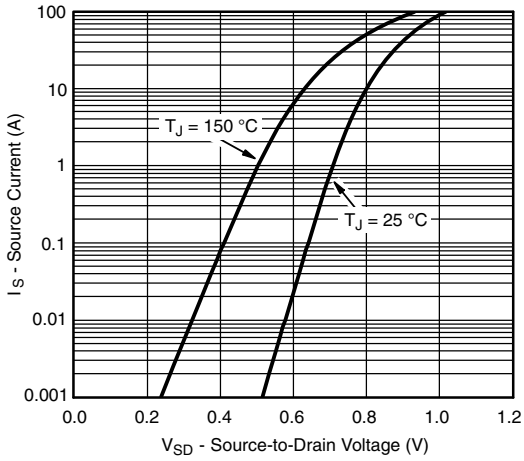
Transconductance



On-Resistance vs. Drain Current

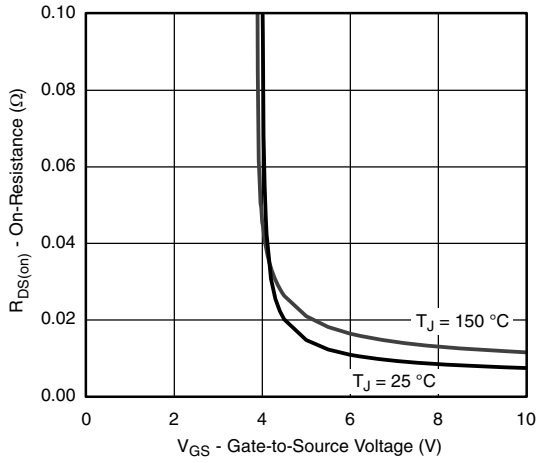


On-Resistance vs. Junction Temperature

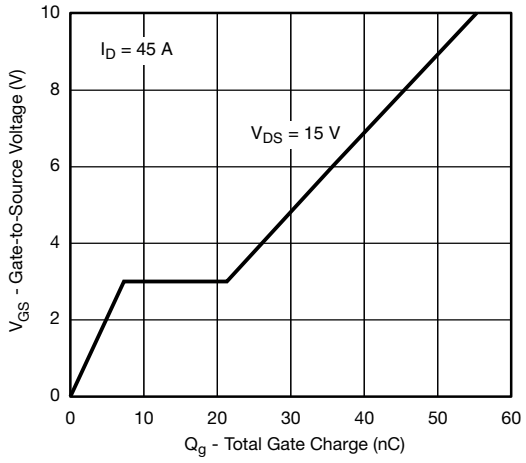


Source Drain Diode Forward Voltage

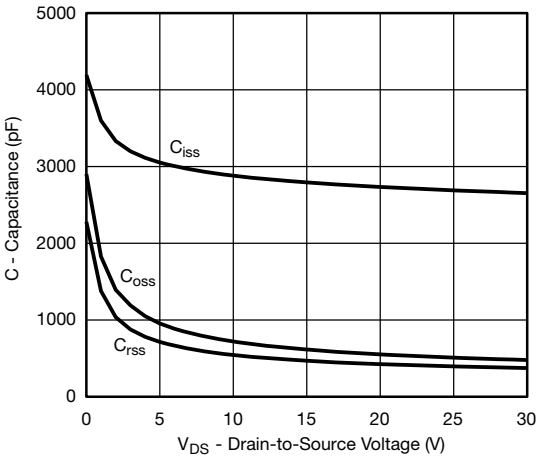
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



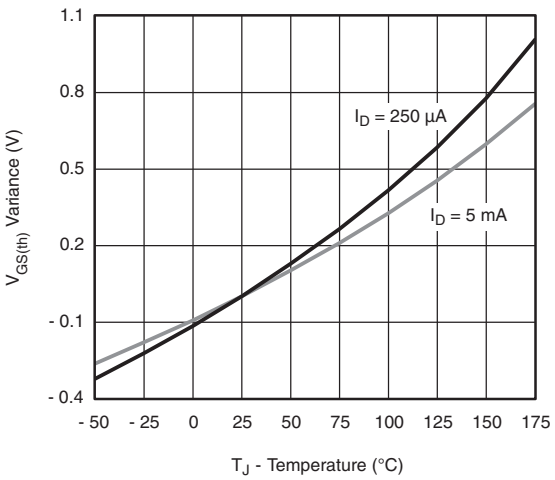
On-Resistance vs. Gate-to-Source Voltage



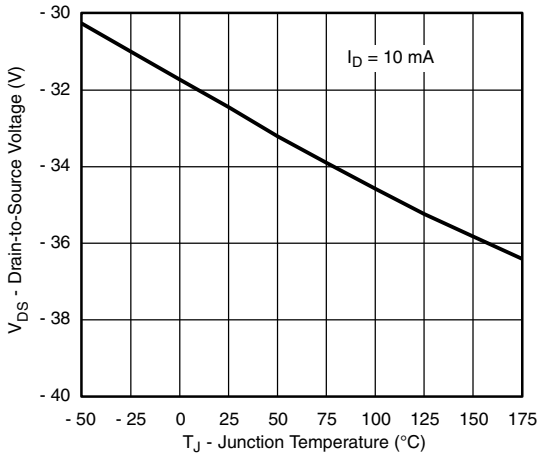
Gate Charge



Capacitance

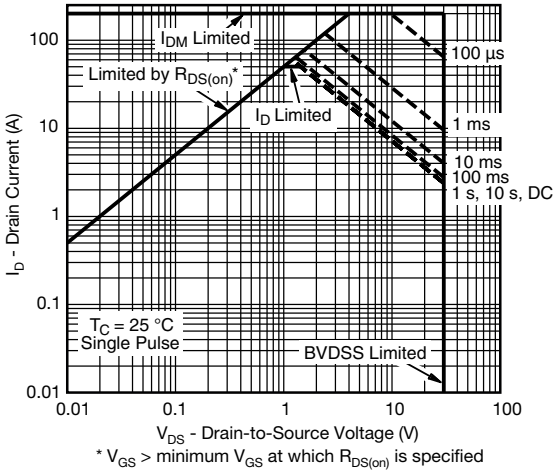


Threshold Voltage

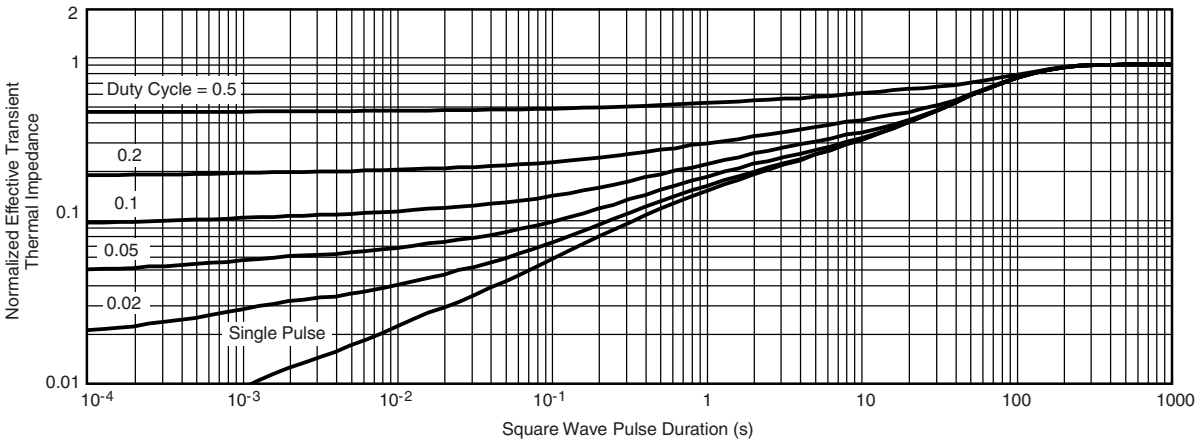


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

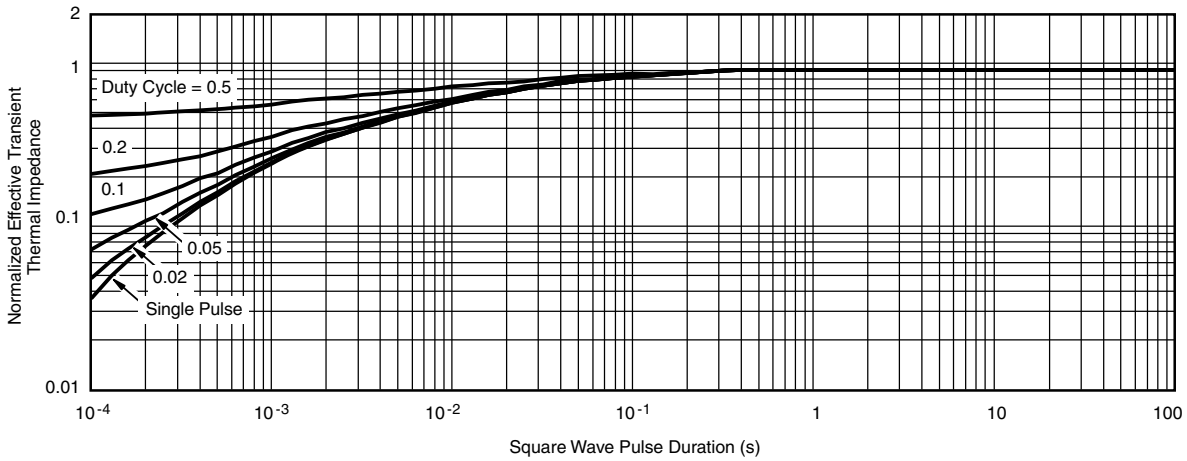


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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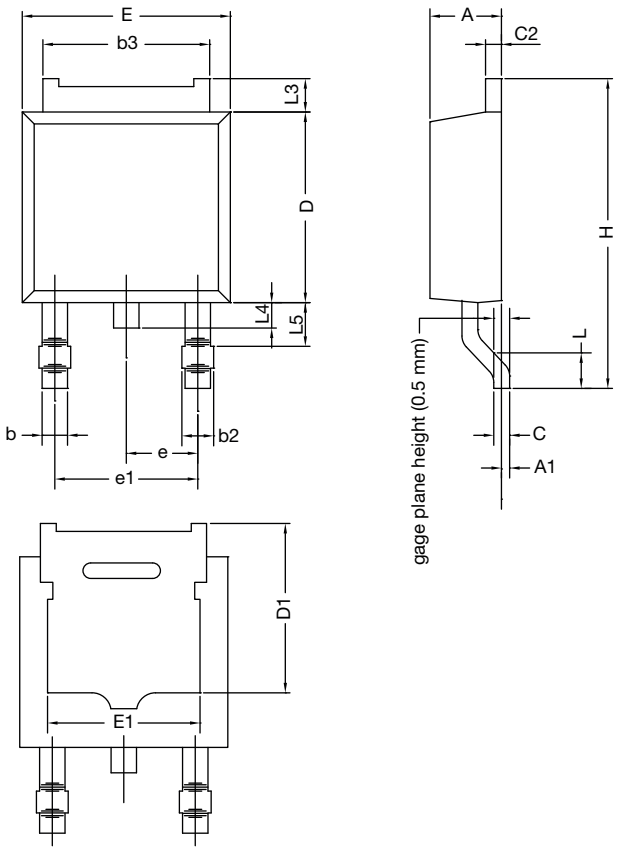
TO-252AA Case Outline

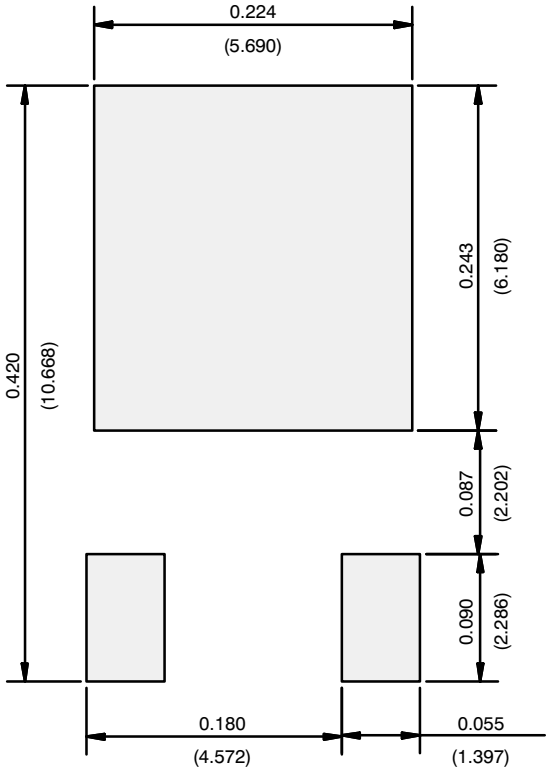


	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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